

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph starting at page 2, line 16, and ending at page 3, line 3, with the following rewritten paragraph:

“However, in recent years, it has been pointed out by Gregory Scott et al. that the drain current of a MOS transistor changes depending on the diffusion length DL thereof, and this has attracted attention as a new factor for lowering simulation accuracy ("NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress" by Gregory Scott and ~~four others~~ et al, IEDM Technical Digest, U.S.A., IEEE, 1999, IEDM-99, p. 827-830). In the case of transistors based on isolation technology, such as STI (Shallow Trench Isolation), as the isolation between transistors becomes finer, it is assumed that the mobility in the channel region under the gate electrode changes under the influence of crystal strain induced in the diffusion layer and the channel region owing to the existence of the isolation regions in the circumference, thereby resulting in the change in drain current.”